



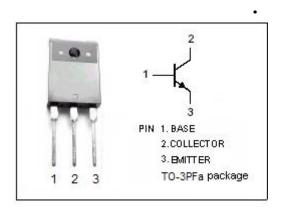
# **isc Silicon NPN Power Transistor**

### **DESCRIPTION**

- · Collector-Base Breakdown Voltage-
  - : V<sub>(BR)CBO</sub>= 900V(Min.)
- Wide Area of Safe Operation
- · High Speed Switching
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

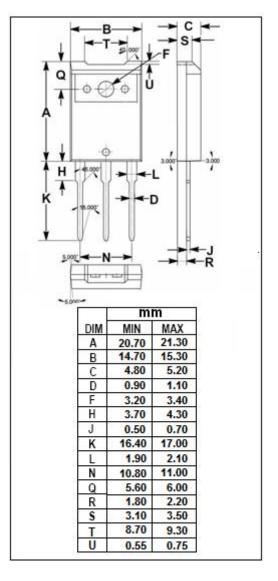
#### **APPLICATIONS**

· Designed for high speed switching applications.



## ABSOLUTE MAXIMUM RATINGS (Ta=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V <sub>CBO</sub>	Collector-Base Voltage	900	V
V <sub>CES</sub>	Collector-Emitter Voltage	900	V
V <sub>CEO</sub>	Collector-Emitter Voltage	800	V
V <sub>EBO</sub>	Emitter-Base Voltage	7	V
Ic	Collector Current-Continuous	4	А
Ісм	Collector Current-Peak	6	А
I <sub>B</sub>	Base Current-Continuous	2	А
Pc	Collector Power Dissipation @T <sub>a</sub> =25℃	3	
	Collector Power Dissipation @T <sub>C</sub> =25°C	70	W
T <sub>j</sub>	Junction Temperature	150	$^{\circ}$ C
T <sub>stg</sub>	Storage Temperature Range	-55~150	$^{\circ}$





## isc Silicon NPN Power Transistor

2SC3980

#### **ELECTRICAL CHARACTERISTICS**

T<sub>C</sub>=25℃ unless otherwise specified

1c-25 C unless otherwise specified								
SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT		
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = 10mA; I <sub>B</sub> = 0	800			V		
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 2A; I <sub>B</sub> = 0.4A			1.5	٧		
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = 2A; I <sub>B</sub> = 0.4A			1.5	٧		
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = 900V; I <sub>E</sub> = 0			50	μ <b>Α</b>		
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 7V; I <sub>C</sub> = 0			50	μ <b>Α</b>		
h <sub>FE-1</sub>	DC Current Gain	I <sub>C</sub> = 0.1A; V <sub>CE</sub> = 5V	8					
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = 2A; V <sub>CE</sub> = 5V	6					
f⊤	Current-Gain—Bandwidth Product	I <sub>C</sub> = 0.2A; V <sub>CE</sub> = 5V; f= 1MHz		15		MHz		
Switching Times								
t <sub>on</sub>	Turn-on Time				0.7	μs		
ts	Storage Time	I <sub>C</sub> = 2A; I <sub>B1</sub> = 0.4A; I <sub>B2</sub> = -0.8A; V <sub>CC</sub> = 250V			2.5	μS		
t <sub>f</sub>	Fall Time				0.3	μS		

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